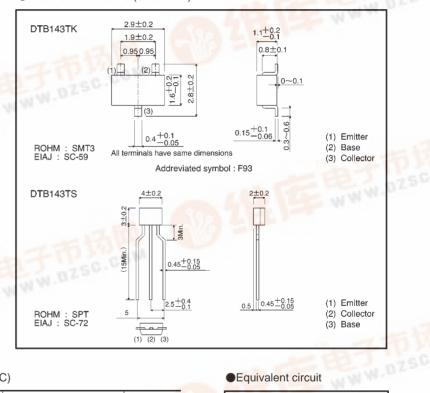
Digital transistors (built in resistor) DTB143TK / DTB143TS

Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thinfilm resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- Structure PNP digital transistor (Built-in resistor type)

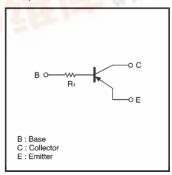
External dimensions (Units: mm)



● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits(D	Unit	
- Farameter	Symbol	K S		
Collector-base voltage	Vсво	-5	V	
Collector-emitter voltage	VCEO	-4	V	
Emitter-base voltage	VEBO	M.As	V	
Collector current	lc	-500		mA
Collector power dissipation	Pc	200	300	mW
Junction temperature	Tj	150		Ç
Storage temperature	Tstg	−55∼+150		C

Equivalent circuit



●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-50	_	_	V	Ic=-50 μ A
Collector-emitter breakdown voltage	BVCEO	-40	_	_	V	Ic=-1mA
Emitter-base breakdown voltage	ВУЕВО	-5	_	_	V	I _E =-50 μ A
Collector cutoff current	Ісво	_	_	一0.5	μΑ	V _{CB} =-50V
Emitter cutoff current	ІЕВО	_	_	一0.5	μΑ	V _{EB} =-4V
Collector-emitter saturation voltage	VCE(sat)	_	_	-0.3	V	Ic/I _B =-50mA/-2.5mA
DC current transfer ratio	hfe	100	250	600	_	V _{CE} =-5V, I _C =-50mA
Input resistance	R ₁	3.29	4.7	6.11	kΩ	_
Transition frequency	fτ		200	_	MHz	Vce=-10V, Ie=50mA, f=100MHz *

^{*} Transition frequency of the device

Packaging specifications

	Package	SMT3	SPT	
	Packaging type	Taping	Taping	
	Code	T146	TP	
Part No.	Basic ordering unit (pieces)	3000	5000	
DTB143TK		0	_	
DTB143TS		_	0	

Electrical characteristic curves

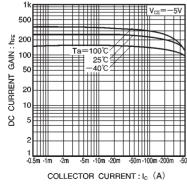


Fig.1 DC current gain vs. collector current

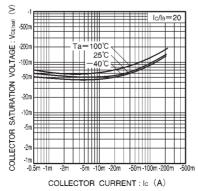


Fig.2 Collector-emitter saturation voltage vs. collector current